

<b>Notice of References Cited</b>	Application/Control No. 09/745,114	Applicant(s)/Patent Under Reexamination YANG, SAM	
	Examiner Scott R. Wilson	Art Unit 2826	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-4,937,650	06-1990	Shinriki et al.	257/296
	B	US-5,558,961	09-1996	Doeff et al.	429/224
	C	US-4,899,203	02-1990	Ino, Masayoshi	257/306
	D	US-5,856,937	01-1999	Chu et al.	365/51
	E	US-5,867,444	02-1999	Le et al.	365/230.06
	F	US-5,177,574	01-1993	Yoneda, Masahiro	257/306
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Time Domain CVD, <a href="http://www.timedomaincvd.com/CVD_Fundamentals/films/Ta2O5.html">http://www.timedomaincvd.com/CVD_Fundamentals/films/Ta2O5.html</a> , High Dielectric constant Materials for DRAMS: Tantalum Oxide. Chart listing dielectric constants of SiO2, Si3N4, Ta2O5, BST
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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